

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP321, TLP321-2, TLP321-4

Programmable Controllers

DC-Output Module

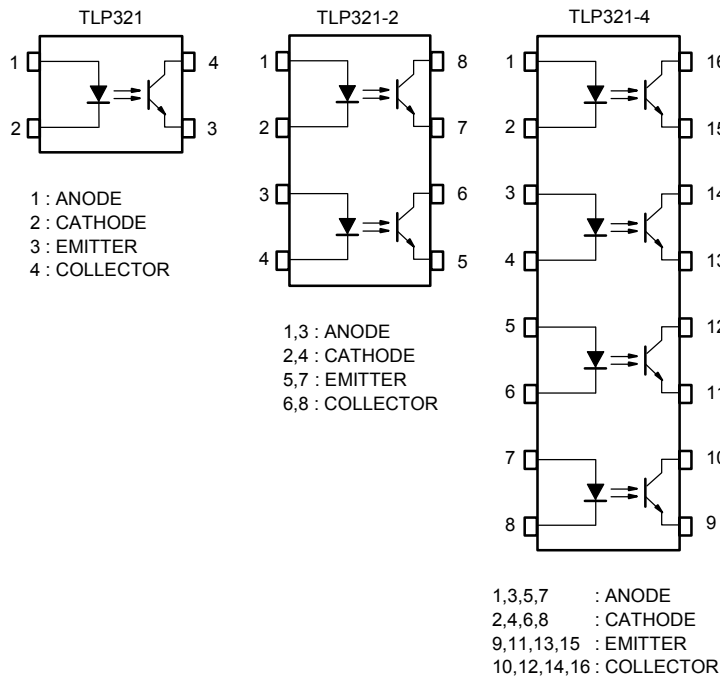
Telecommunication

The TOSHIBA TLP321, -2 and -4 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode. The TLP321-2 offers two isolated channels in an eight lead plastic DIP package, while the TLP321-4 provides four isolated channels in a sixteen plastic DIP package.

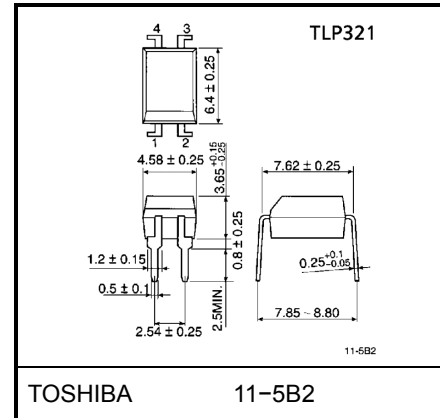
TLP321 / -2 / -4 have high VCEO voltage (VCEO = 80V).

- Collector-emitter voltage: 80V (min.)
- Current transfer ratio: 50% (min.)
Rank GB: 100% (min.)
- Isolation voltage: 5000Vrms (min.)
- UL recognized: UL1577, file no. E67349

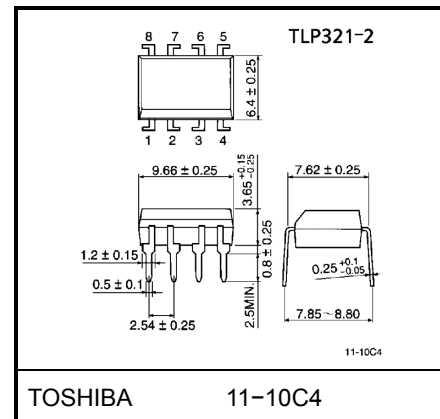
Pin Configurations (top view)



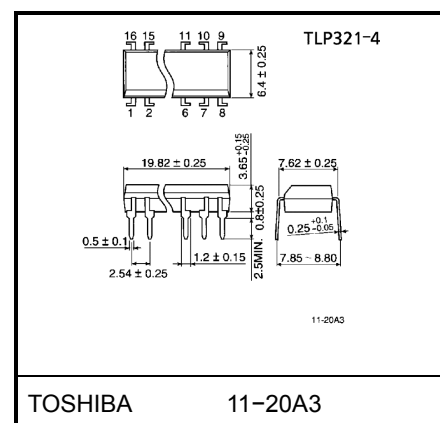
Unit in mm



Weight: 0.26g



Weight: 0.54g



Weight: 1.1g

Current Transfer Ratio

Type	Classification *1	Current Transfer Ratio (%) (I _C / I _F)		Marking Of Classification
		I _F = 5mA, V _{CE} = 5V, Ta = 25°C		
		Min.	Max.	
TLP321	(None)	50	600	BLANK, Y, Y [■] , G, G [■] , B, B [■] , GB
	Rank Y	50	150	Y, Y [■]
	Rank GR	100	300	G, G [■]
	Rank BL	200	600	B, B [■]
	Rank GB	100	600	G, G [■] , B, B [■] , GB
TLP321-2	(None)	50	600	BLANK, GR, BL, GB
TLP321-4	Rank GB	100	600	GR, BL, GB

*1: Ex. Rank GB: TLP321 (GB)

(Note) Application type name for certification test, please use standard product type name, i. e.

TLP321 (GB): TLP321

TLP321-2 (GB): TLP321-2

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating		Unit
			TLP321-1	TLP321-2 TLP321-4	
LED	Forward current	I_F	60	50	mA
	Forward current derating	$\Delta I_F / ^\circ\text{C}$	-0.7 (Ta $\geq 39^\circ\text{C}$)	-0.5 (Ta $\geq 25^\circ\text{C}$)	mA / $^\circ\text{C}$
	Pulse forward current	I_{FP}	1 (100 μs pulse, 100pps)		A
	Reverse voltage	V_R	5		V
	Junction temperature	T_j	125		$^\circ\text{C}$
Detector	Collector-emitter voltage	V_{CEO}	80		V
	Emitter-collector voltage	V_{ECO}	7		V
	Collector current	I_C	50		mA
	Collector power dissipation (1 Circuit)	P_C	150	100	mW
	Collector power dissipation derating (1 Circuit, Ta $\geq 25^\circ\text{C}$)	$\Delta P_C / ^\circ\text{C}$	-1.5	-1.0	mW / $^\circ\text{C}$
	Junction temperature	T_j	125		$^\circ\text{C}$
Storage temperature range		T_{stg}	-55~125		$^\circ\text{C}$
Operating temperature range		T_{opr}	-55~100		$^\circ\text{C}$
Lead soldering temperature		T_{sol}	260 (10s)		$^\circ\text{C}$
Total package power dissipation		R_T	250	150	mW
Total package power dissipation derating (Ta $\geq 25^\circ\text{C}$)		$\Delta P_T / ^\circ\text{C}$	-2.5	-1.5	mW / $^\circ\text{C}$
Isolation voltage (Note 1)		BV_S	5000 (AC, 1min., RH $\leq 60\%$)		Vrms

(Note 1) Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	12	48	V
Forward current	I_F	—	16	20	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	-25	—	85	°C

Individual Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic		Symbol	Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
	Reverse current	I _R	V _R = 5 V	—	—	10	μA
	Capacitance	C _T	V = 0, f = 1MHz	—	30	—	pF
Detector	Collector–emitter breakdown voltage	V _(BR) CEO	I _C = 0.5mA	80	—	—	V
	Emitter–collector breakdown voltage	V _(BR) ECO	I _E = 0.1mA	7	—	—	V
	Collector dark current	I _{CEO}	V _{CE} = 48V	—	10	100	nA
			V _{CE} = 48V, Ta = 85°C	—	2	50	μA
	Capacitance (collector to emitter)	C _{CE}	V = 0, f = 1MHz	—	10	—	pF

Coupled Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1 \text{ mA}, V_{CE} = 0.4 \text{ V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-emitter saturation voltage	$V_{CE} (\text{sat})$	$I_C = 2.4 \text{ mA}, I_F = 8 \text{ mA}$	—	—	0.4	V
		$I_C = 0.2 \text{ mA}, I_F = 1 \text{ mA}$ Rank GB	—	0.2	—	
			—	—	0.4	

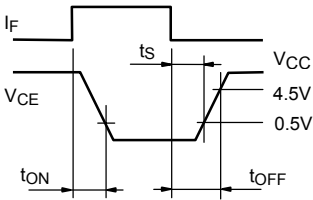
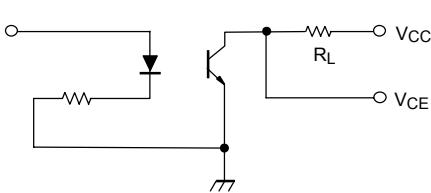
Isolation Characteristics (Ta = 25°C)

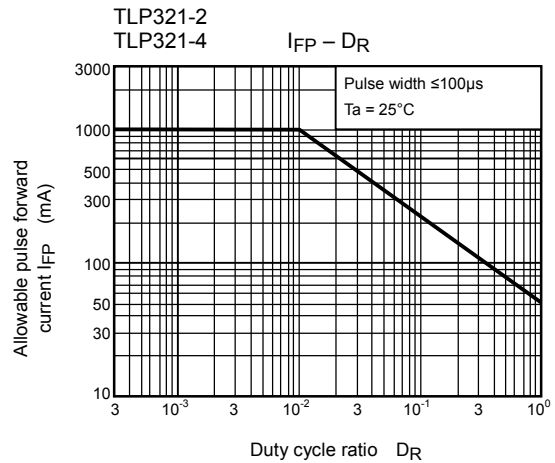
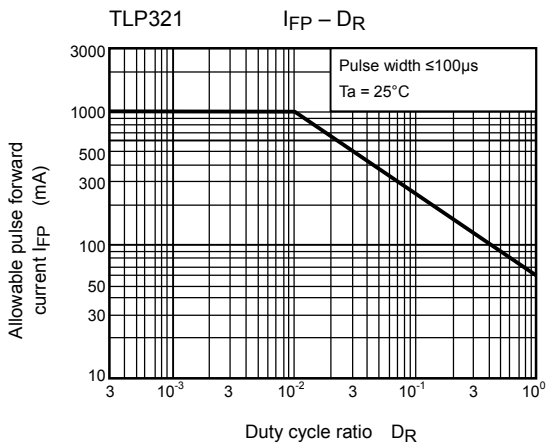
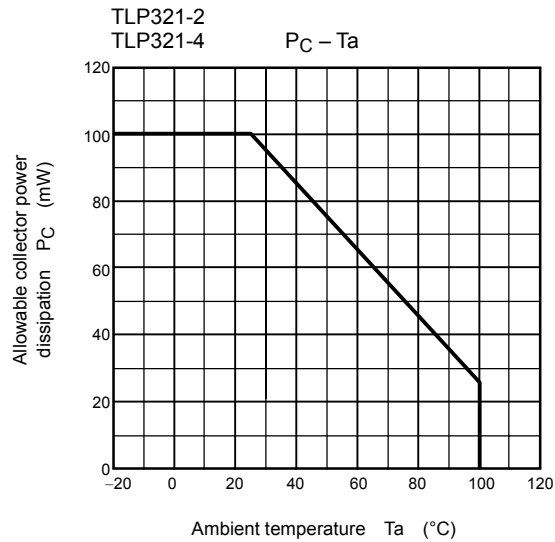
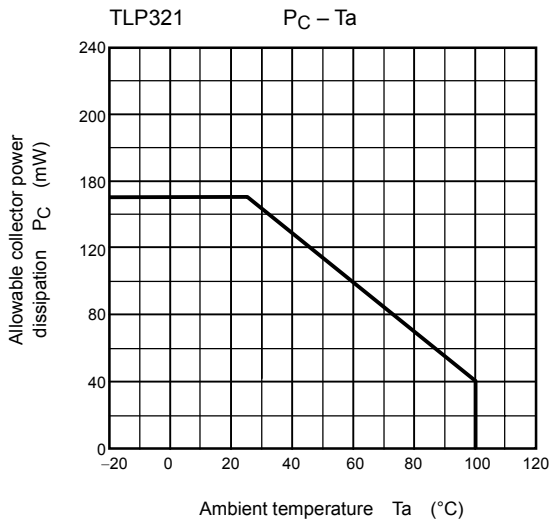
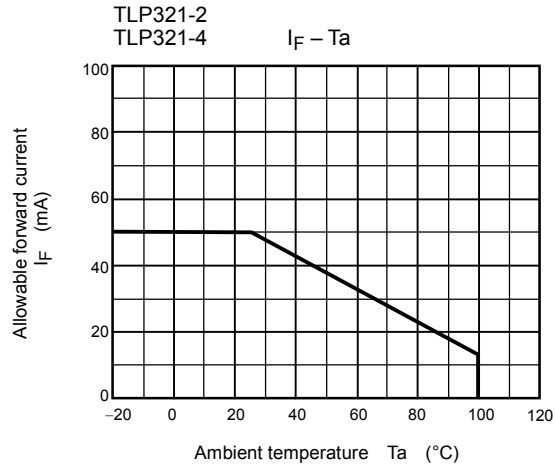
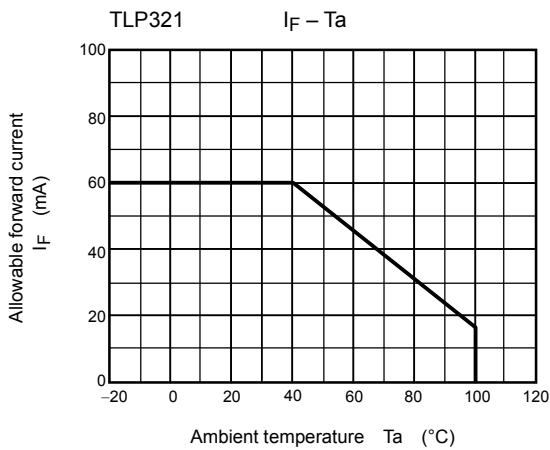
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	CS	VS = 0, f = 1MHz	—	0.8	—	pF
Isolation resistance	RS	VS = 500V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation voltage	BVS	AC, 1 minute	5000	—	—	Vrms
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	Vdc

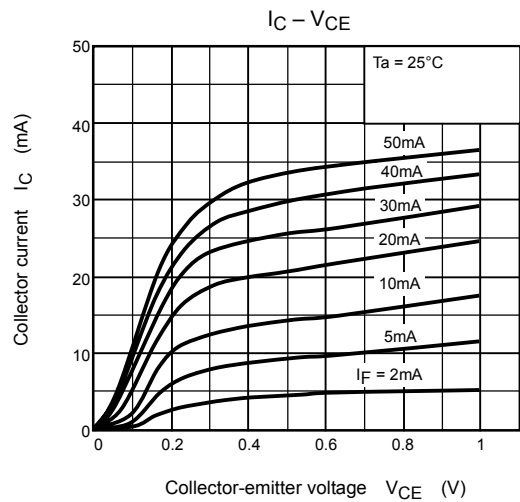
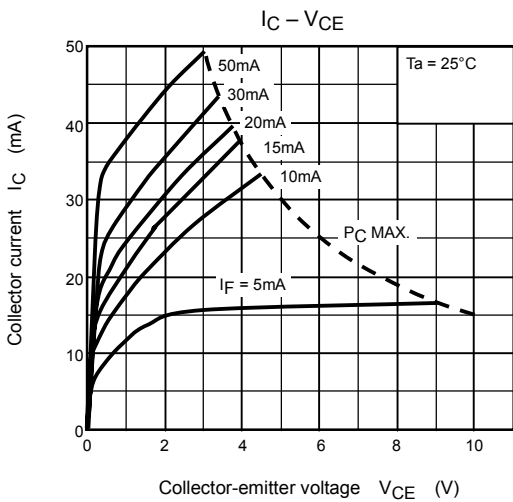
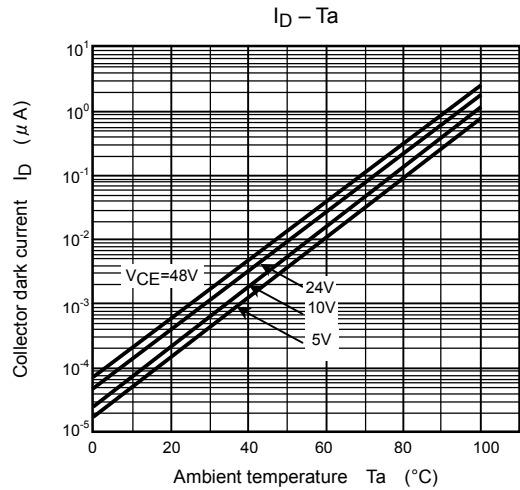
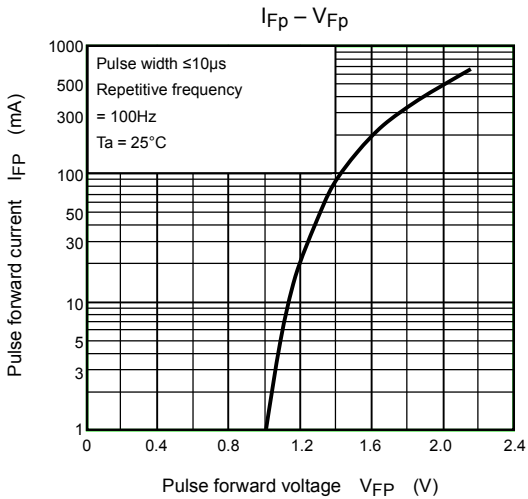
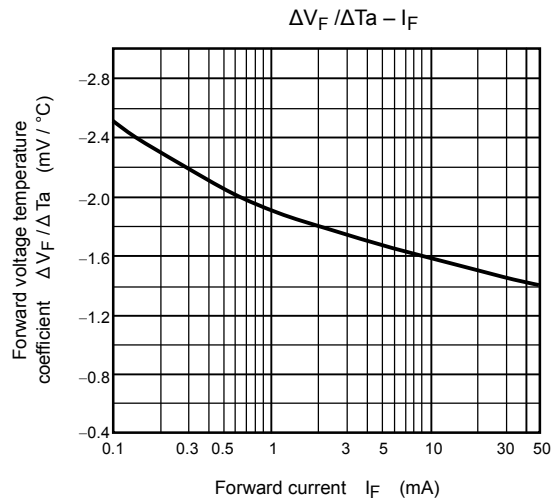
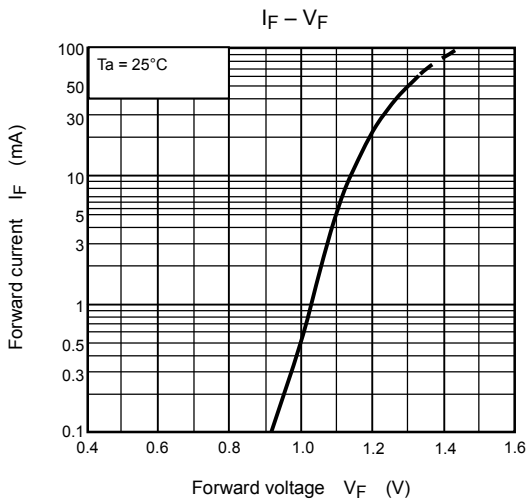
Switching Characteristics (Ta = 25°C)

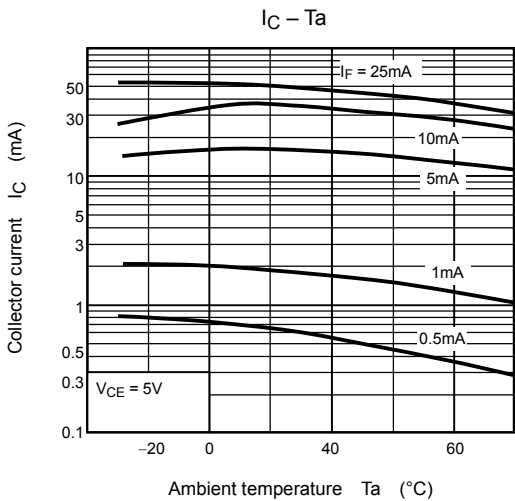
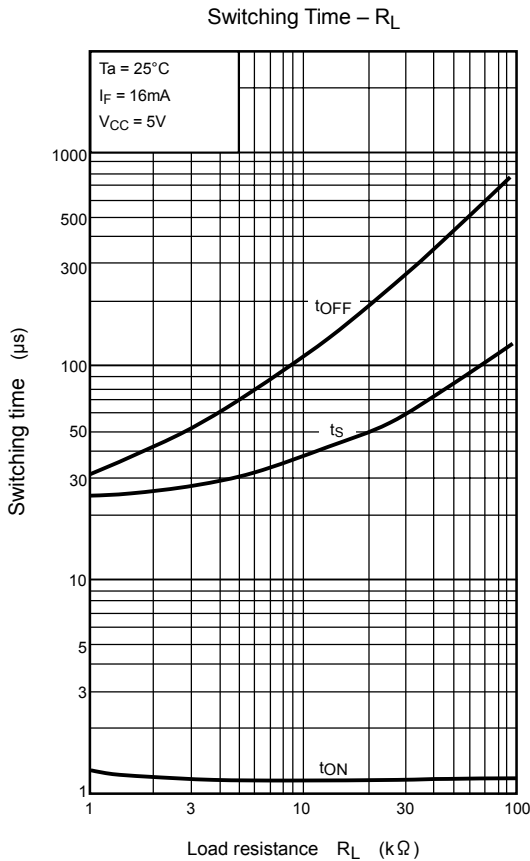
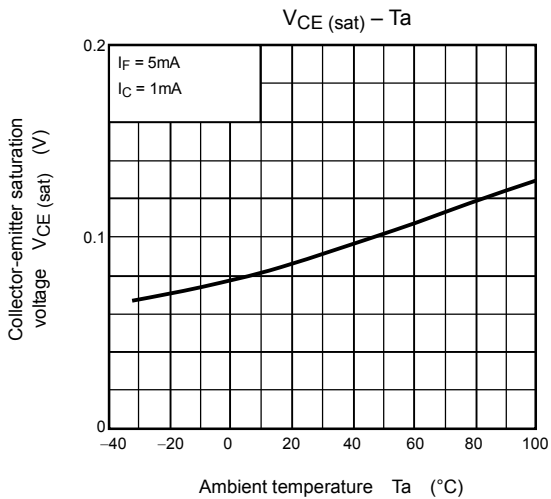
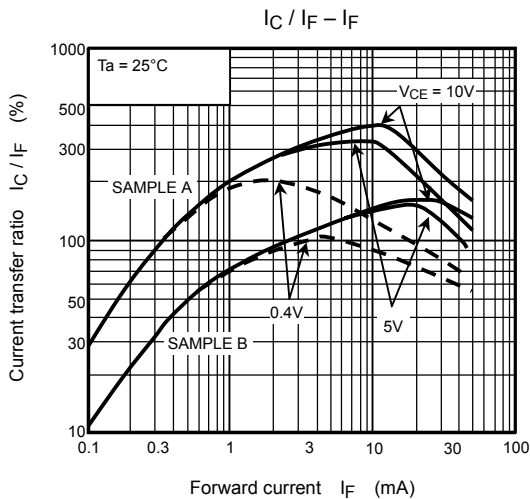
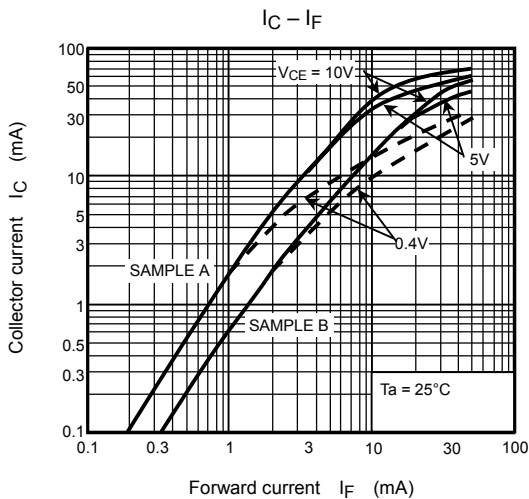
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	tr	VCC = 10V IC = 2mA RL = 100Ω	—	2	—	μs
Fall time	tf		—	3	—	
Turn-on time	ton		—	3	—	
Turn-off time	toff		—	3	—	
Turn-on time	tON	RL = 1.9kΩ (Fig.1) VCC = 5V, IF = 16mA	—	2	—	μs
Storage time	ts		—	15	—	
Turn-off time	tOFF		—	25	—	

Fig. 1 Switching time test circuit









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000707EBC

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